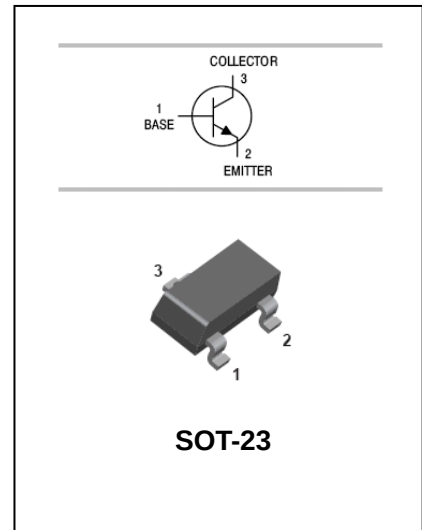


## NPN SWITCHING TRANSISTOR

## MMBT3904

### FEATURES

- Epitaxial planar die construction.
- Complementary PNP type available (MMBT3906).
- Collector Current Capability  $I_{CM} = 200\text{mA}$ .
- Collector-emitter Voltage  $V_{CEO} = 40\text{V}$ .



### APPLICATIONS

- General switching and amplification

### ORDERING INFORMATION

| Type No. | Marking | Package Code |
|----------|---------|--------------|
| MMBT3904 | 1AM     | SOT-23       |

### MAXIMUM RATING @ $T_a = 25^\circ\text{C}$ unless otherwise specified

| SYMBOL    | PARAMETER                     | CONDITIONS                      | Value       | UNIT             |
|-----------|-------------------------------|---------------------------------|-------------|------------------|
| $V_{CBO}$ | collector-base voltage        | open emitter                    | 60          | V                |
| $V_{CEO}$ | collector-emitter voltage     | open base                       | 40          | V                |
| $V_{EBO}$ | emitter-base voltage          | open collector                  | 6           | V                |
| $I_C$     | collector current (DC)        |                                 | 100         | mA               |
| $I_{CM}$  | peak collector current        |                                 | 200         | mA               |
| $I_{BM}$  | peak base current             |                                 | 100         | mA               |
| $P_{tot}$ | total power dissipation       | $T_{amb} \leq 25^\circ\text{C}$ | 250         | mW               |
| $T_{stg}$ | storage temperature           |                                 | -65 to +150 | $^\circ\text{C}$ |
| $T_j$     | junction temperature          |                                 | 150         | $^\circ\text{C}$ |
| $T_{amb}$ | operating ambient temperature |                                 | -65 to +150 | $^\circ\text{C}$ |



## NPN SWITCHING TRANSISTOR

## MMBT3904

### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

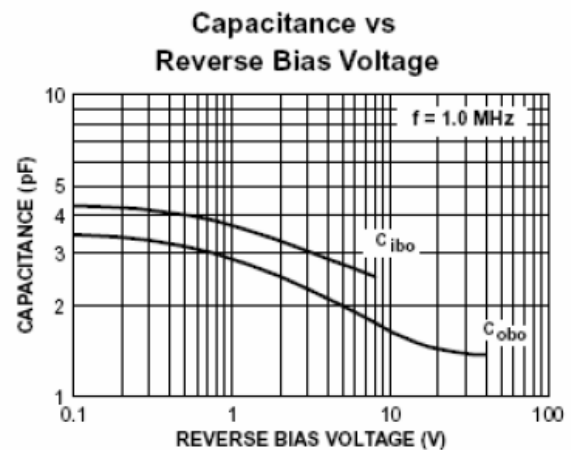
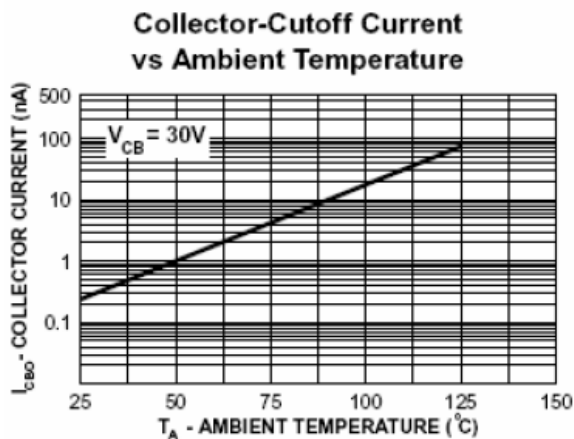
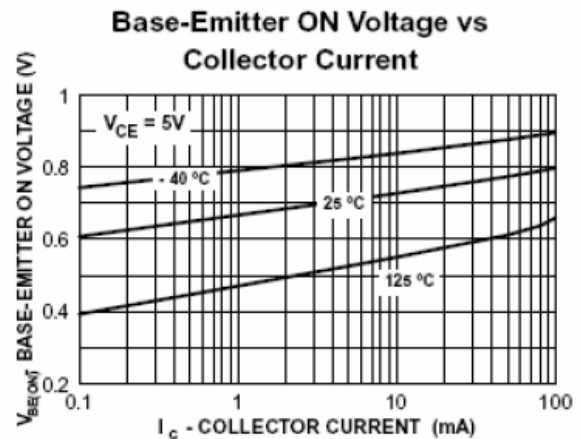
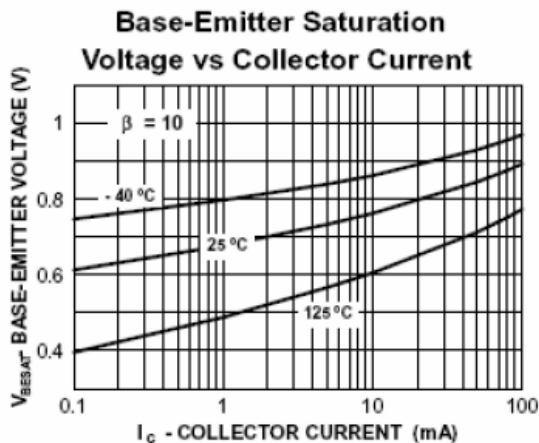
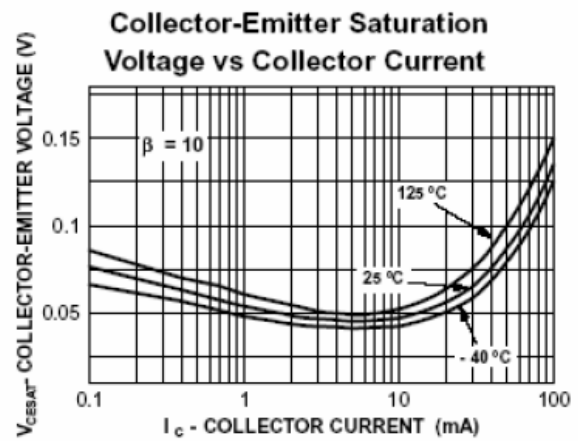
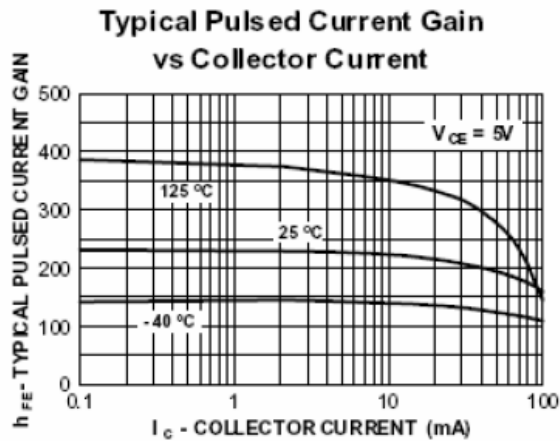
| SYMBOL                                        | PARAMETER                            | CONDITIONS                                                                                                    | MIN. | MAX. | UNIT |
|-----------------------------------------------|--------------------------------------|---------------------------------------------------------------------------------------------------------------|------|------|------|
| $I_{CBO}$                                     | collector cut-off current            | $I_E = 0; V_{CB} = 30\text{ V}$                                                                               | -    | 50   | nA   |
| $I_{EBO}$                                     | emitter cut-off current              | $I_C = 0; V_{EB} = 6\text{ V}$                                                                                | -    | 50   | nA   |
| $h_{FE}$                                      | DC current gain                      | $V_{CE} = 1\text{ V};$<br>$I_C = 0.1\text{ mA}$                                                               | 60   | -    |      |
|                                               |                                      | $I_C = 1\text{ mA}$                                                                                           | 80   | -    |      |
|                                               |                                      | $I_C = 10\text{ mA}$                                                                                          | 100  | 300  |      |
|                                               |                                      | $I_C = 50\text{ mA}$                                                                                          | 60   | -    |      |
|                                               |                                      | $I_C = 100\text{ mA}$                                                                                         | 30   | -    |      |
|                                               |                                      |                                                                                                               |      |      |      |
| $V_{CE(sat)}$                                 | collector-emitter saturation voltage | $I_C = 10\text{ mA}; I_B = 1\text{ mA}$                                                                       | -    | 200  | mV   |
|                                               |                                      | $I_C = 50\text{ mA}; I_B = 5\text{ mA}$                                                                       | -    | 300  | mV   |
| $V_{BE(sat)}$                                 | base-emitter saturation voltage      | $I_C = 10\text{ mA}; I_B = 1\text{ mA}$                                                                       | 650  | 850  | mV   |
|                                               |                                      | $I_C = 50\text{ mA}; I_B = 5\text{ mA}$                                                                       | -    | 950  | mV   |
| $C_c$                                         | collector capacitance                | $I_E = I_C = 0; V_{CB} = 5\text{ V};$<br>$f = 1\text{ MHz}$                                                   | -    | 4    | pF   |
| $C_e$                                         | emitter capacitance                  | $I_C = I_E = 0; V_{BE} = 500\text{ mV};$<br>$f = 1\text{ MHz}$                                                | -    | 8    | pF   |
| $f_T$                                         | transition frequency                 | $I_C = 10\text{ mA}; V_{CE} = 20\text{ V};$<br>$f = 100\text{ MHz}$                                           | 300  | -    | MHz  |
| F                                             | noise figure                         | $I_C = 100\text{ mA}; V_{CE} = 5\text{ V};$<br>$R_S = 1\text{ k}\Omega; f = 10\text{ Hz to } 15.7\text{ kHz}$ | -    | 5    | dB   |
| Switching times (between 10% and 90% levels); |                                      |                                                                                                               |      |      |      |
| $t_d$                                         | delay time                           | $I_{Con} = 10\text{ mA}; I_{Bon} = 1\text{ mA};$<br>$I_{Boff} = -1\text{ mA}$                                 | -    | 35   | ns   |
| $t_r$                                         | rise time                            |                                                                                                               | -    | 35   | ns   |
| $t_s$                                         | storage time                         |                                                                                                               | -    | 200  | ns   |
| $t_f$                                         | fall time                            |                                                                                                               | -    | 50   | ns   |

Note Pulse test:  $t_p \leq 300\text{ ms}; d \leq 0.02$ .

## NPN SWITCHING TRANSISTOR

## MMBT3904

TYPICAL CHARACTERISTICS @  $T_a = 25^\circ\text{C}$  unless otherwise specified



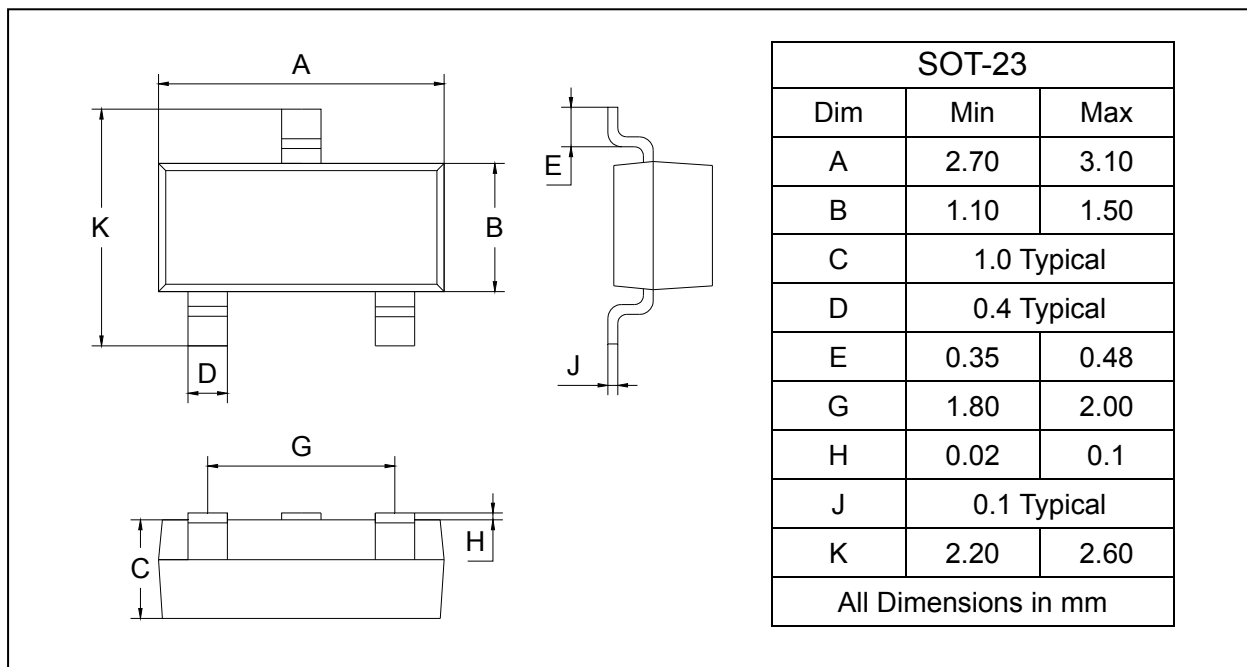
## NPN SWITCHING TRANSISTOR

## MMBT3904

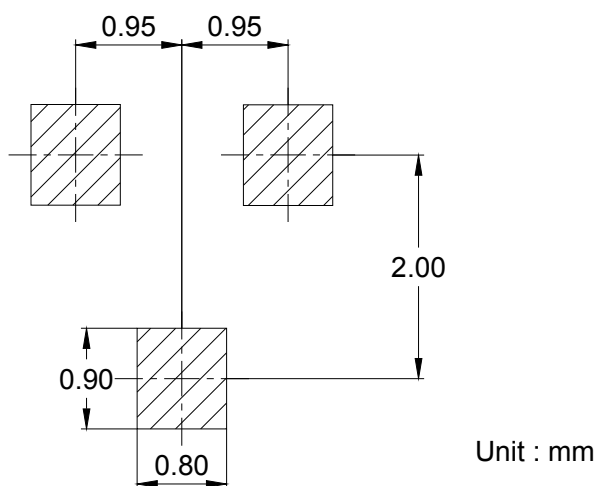
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

| Device   | Package | Shipping       |
|----------|---------|----------------|
| MMBT3904 | SOT-23  | 3000/Tape&Reel |